

Spin-dependent transport in a clean one-dimensional channel

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(February 7, 2008)

A shoulder-like feature close to $(0.7 \times 2e^2/h)$, “the *0.7 structure*” at zero magnetic field was observed in clean one-dimensional (1D) channels [K.J. Thomas *et al.*, Phys. Rev. Lett. 77, 135 (1996)]. To provide further understanding of this structure, we have performed low-temperature measurements of a novel design of 1D channel with overlaying finger gates to study the 0.7 structure as a function of lateral confinement strength and potential profile. We found that the structure persists when the lateral confinement strength is changed by a factor of 2. We have also shown that the 0.7 structure present in two 1D channels in series behaves like a single 1D channel which shows the 0.7 structure, demonstrating that the 0.7 structure is not a transmission effect through a ballistic channel at zero in-plane magnetic field.

PACS numbers: 73.40.Gk, 73.20.Dx, 73.40.-c

Using the now well-established electrostatic squeezing split-gate technique [1], it is possible to define a one-dimensional (1D) channel within a two-dimensional electron gas (2DEG). If the elastic scattering length is longer than the 1D channel length, one may observe ballistic conductance plateaus quantized in units of $2e^2/h$ [2,3] at zero magnetic field, where the factor of 2 arises from the electron spin degeneracy. When a large magnetic field is applied parallel to the 1D channel, such that the electron spin degeneracy is lifted, conductance plateaus quantized in units of e^2/h are observed [4]. Quantized conductance plateaus in units of $2e^2/h$ at zero magnetic field (e^2/h at high parallel fields) observed in a 1D channel can be well explained by cancellation of the Fermi velocity and 1D density of states within a single-particle picture.

In very clean 1D channels a clear plateau-like structure close to $(0.7 \times 2e^2/h)$ has been observed at zero magnetic field $B = 0$ [5]. This “*0.7 structure*” whose conductance value is placed between the spin-degenerate conductance plateau at $2e^2/h$ and the spin-split conductance plateau at e^2/h , cannot be explained within a single-particle picture. The fact that the 0.7 structure evolves into a $(0.5 \times 2e^2/h)$ spin-split conductance plateau on the application of an in-plane magnetic field suggests the structure is related to spin. The 0.7 structure has also been observed in 1D channels with different sample designs [5–7], establishing that it is a universal effect. In particular, Kristensen *et al.* [8] reported activated behaviour of the 0.7 structure as a function of temperature with a density-dependent activation temperature of around 2 K. Various theoretical models [9,10] involving partial transmission [11,12] and hybridization of different spin states [13] have been proposed to explain this undisputed result, however, its exact physical origin is still unknown. It is the purpose of this paper to report further experimental studies.

We have designed a novel 1D channel with three separate and independently contacted overlaying finger gates.

It is well known that the potential profile of a ballistic 1D channel is often best described by a saddle point potential [14] with both lateral and longitudinal confinement. By changing the applied voltages on the overlaying gate fingers above the 1D channel, we are able to vary both the lateral confinement strength and the potential profile within the channel. We find that the 0.7 structure is an intrinsic property of a clean 1D channel well over the range investigated. Moreover, we shall present experimental evidence that the 0.7 structure is not a transmission effect at zero in-plane magnetic field.

Figure 1 (a) shows a schematic diagram of the device configuration. The device was defined by electron beam lithography on the surface of the sample T258, 157 nm above a two-dimensional electron gas (2DEG). There is a 30 nm-thick layer of polymethylmethacrylate (PMMA) which has been highly dosed by an electron beam, to act as a dielectric [15] between the split-gate and three gate fingers so that all gates can be independently controlled [16]. The carrier concentration of the 2DEG was $1.9 \times 10^{15} \text{ m}^{-2}$ with a mobility of $250 \text{ m}^2/\text{Vs}$ after brief illumination with a red light emitting diode. The transport mean free path is $16.5 \text{ }\mu\text{m}$, much longer than the effective 1D channel length. Experiments were performed in a pumped ^3He cryostat and the two-terminal conductance $G = dI/dV$ was measured using an ac excitation voltage of $10 \text{ }\mu\text{V}$ with standard phase-sensitive techniques. In all cases, a zero-split-gate-voltage series resistance ($\approx 900 \text{ }\Omega$) is subtracted from the raw data. The in-plane magnetic field $B_{\parallel}$ is applied parallel to the source-drain current. Three different samples on five different runs showed similar behaviour, and the data that we present here are obtained from two devices A and B at three different cooldowns.

To demonstrate the high-quality of our 1D channel, figure 1 (b) shows the conductance measurements $G(V_{SG})$ as a function of split-gate voltage V_{SG} when all finger gate voltages V_{F1} , V_{F2} and V_{F3} are zero at $T = 300 \text{ mK}$.

We observe conductance plateaus at multiples of $2e^2/h$, with no resonant feature superimposed on top, demonstrating that we have a clean 1D channel in our system in which impurity scattering is negligible. In addition, we also observe the 0.7 structure.

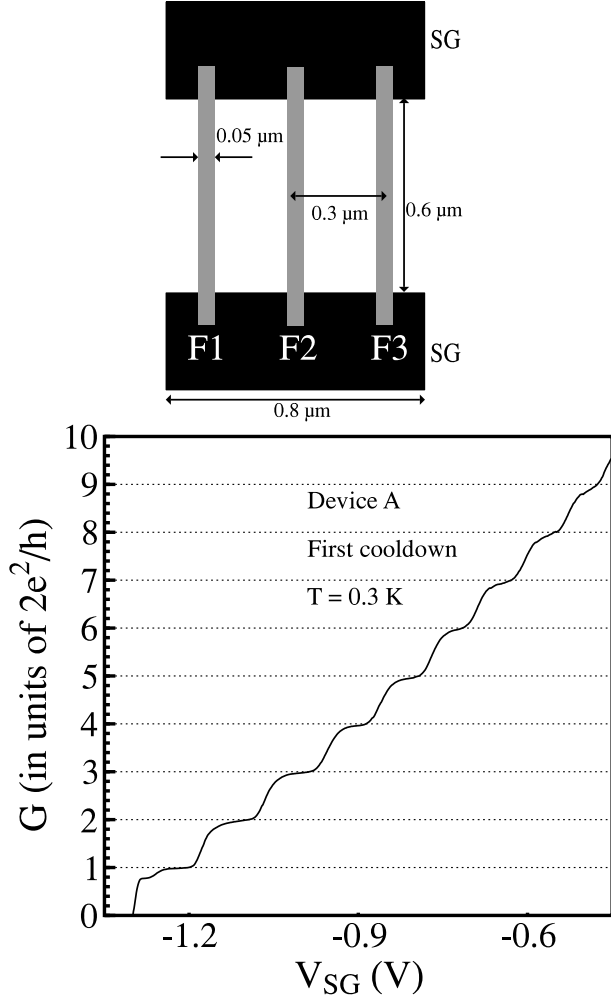


FIG. 1. (a) Schematic diagram showing the device configuration. The grey regions correspond to finger gates, labelled as F1, F2, and F3 lying above the split-gate (labelled as SG), with an insulating layer of crosslinked PMMA in between. (b) $G(V_{SG})$ for all finger gates at 0 V. The measurement temperature was 300 mK.

We now describe the effects of applying a negative finger gate voltage V_{F2} . Figure 2 (a) shows $G(V_{SG})$ for various voltages on F2 while F1 and F3 are at 0 V. The results presented here are taken at a measurement temperature of 1.2 K since the 0.7 structure is known to be more pronounced at higher temperatures [5]. Increasing the negative voltage on F2 decreases the electron density underneath the finger gate. We use a technique developed by Patel *et al.* [17] to measure the energy separation of 1D subbands from the effects of an applied dc source-drain voltage V_{sd} at various V_{F2} . The results are

presented in Fig. 2 (b), and demonstrate a good linear fit $\Delta E_{1,2} = (0.915V_{F2}/V + 2.71)$ (meV). It can be seen that as V_{F2} is made more negative, the energy spacing between the first and $\Delta E_{1,2}(V_{SG})$ decreases, giving rise to the reduction in flatness of the conductance plateaus presented in Fig. 2 (a). Using the saddle point model [14], we estimate the value ω_y/ω_x to decrease from 1.1 to 0.6 over the measurement range $-0.3 \text{ V} \geq V_{F2} \geq -1.8 \text{ V}$. Whilst the 1D ballistic conductance plateaus are no longer distinguishable, the shoulder-like structure close at $G = (0.7 \times 2e^2/h)$ is observed to persist despite this change in the lateral confinement strength. The data shown in figure 2 (a) provide compelling evidence that the 0.7 structure is intrinsic to a clean 1D channel and persists over a wide range of lateral confinement strengths.

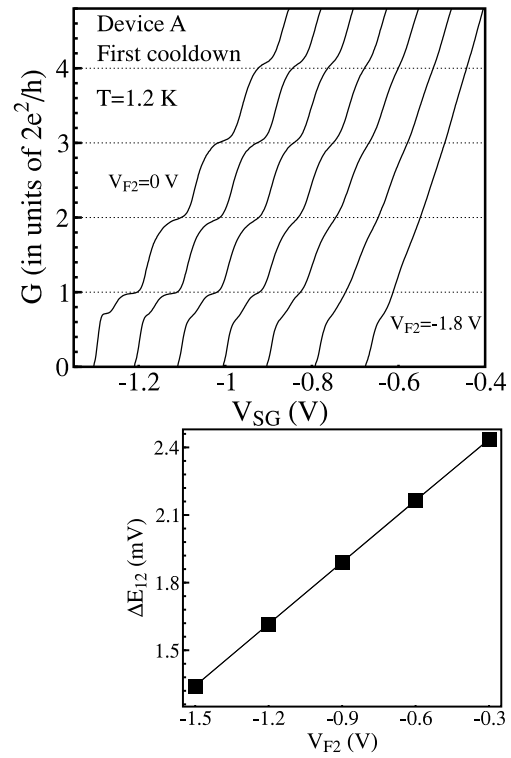


FIG. 2. (a) $G(V_{SG})$ for $V_{F2} = 0$ to -1.8 V in 0.3 V steps when $V_{F1} = V_{F3} = 0 \text{ V}$. The measurement temperature was 1.2 K. (b) $\Delta E_{1,2}(V_{SG})$ (marked by squares) determined by the source-drain bias technique. The linear fit is discussed in the text.

To demonstrate the observed shoulder-like structure close to $(0.7 \times 2e^2/h)$, where the conductance steps are not well-quantized and pronounced, has the same physical origin as those observed which coexist with well-quantized conductance steps [5], we have measured $G(V_{SG})$ at various $B_{\parallel}$. As the applied $B_{\parallel}$ is increased, the shoulder-like feature indeed evolves into a spin-split $(0.5 \times 2e^2/h)$ conductance plateau, as clearly shown in

figure 3, in agreement with early studies of Thomas *et al.* [5]. The fact that the structure at $(0.7 \times 2e^2/h)$ is not replicated at $0.7 \times e^2/h$ when the spin degeneracy is removed at high $B_{\parallel}$ previously reported by Thomas *et al.* [5] and also shown here is evidence that the 0.7 structure is not a transmission effect.

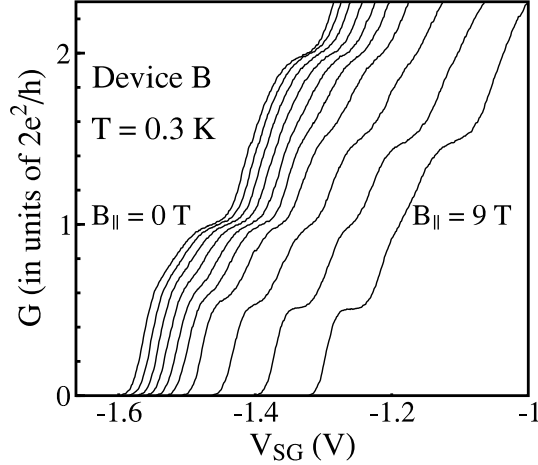


FIG. 3. $G(V_{SG})$ at various applied in-plane magnetic fields $B_{\parallel}$ for $V_{F2} = -1.4$ V and $V_{F1} = V_{F3} = 0$ V. From left to right: $B_{\parallel} = 0$ to 9 T in 1 T steps. Successive traces have been horizontally offset by 3 mV for clarity. The measurement temperature was 300 mK.

Finally we present clear experimental evidence that the 0.7 structure is not a transmission effect in zero in-plane magnetic field. The solid line in figure 4 shows $G(V_{SG})$ when $V_{F1} = -0.22$ V, $V_{F2} = 0$ V and $V_{F3} = 0$, and the dotted line shows $G(V_{SG})$ when $V_{F1} = 0$ V, $V_{F2} = 0$ V and $V_{F3} = -0.3$ V. In both cases, we observe the 0.7 structure at the same V_{SG} so that the two barriers underneath gate fingers are of the same heights. If we now set $V_{F1} = -0.22$ V, $V_{F2} = 0$ and $V_{F3} = -0.3$ V, we obtain the dashed line in figure 4. From the data for $V_{F1} = V_{F2} = V_{F3} = 0$, we know that for $V_{SG} = -2.67$ V there are two 1D subbands present in the ballistic channel defined by SG. As illustrated in Fig. 4, the 1D channel pinches off at $V_{SG} = -2.67$ V for both cases when $V_{F1} = -0.22$ V and $V_{F3} = 0$, and $V_{F1} = 0$ and $V_{F3} = -0.3$ V. The distance between F1 and F3 is twice as much as the distance between F1 (F3) and the underlying 2DEG. Also the presence of the grounded F2 varies the flow of the electric field lines emitted from F1 and F3, which makes the 2DEG regions underneath F2 less affected by the fringing fields from F1 and F3. All these results demonstrate that for $V_{F1} = -0.22$ V, $V_{F2} = 0$ and $V_{F3} = -0.3$ V, we have two narrower 1D constrictions underneath F1 and F3 in series, present in the ballistic channel defined by SG, as illustrated in Fig. 5. Here we estimate the constriction width underneath F1 (F3). Assume that the lateral (the y component) confining po-

tential in the 1D channel has a form

$$U(y) = U(0) + \frac{1}{2}m^*\omega_y^2y^2, \quad (1)$$

where $m^* = 0.067m_e$ and m_e is the electron mass.

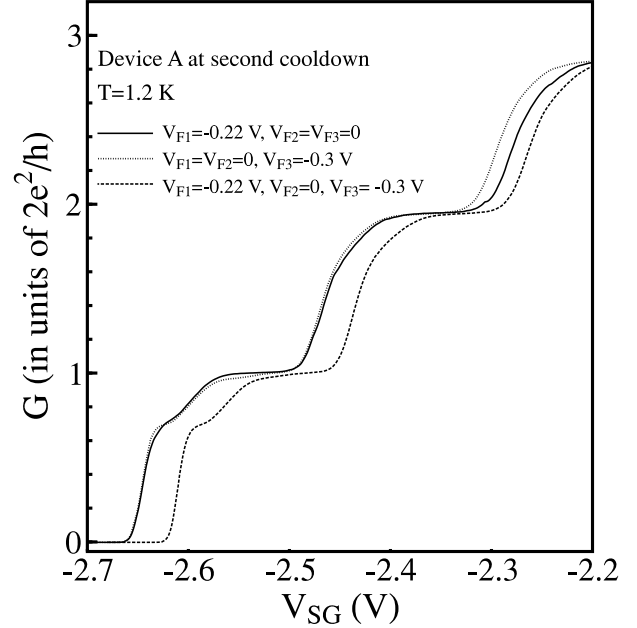


FIG. 4. The solid line shows $G(V_{SG})$ when $V_{F1} = -0.22$ V, $V_{F2} = 0$ V and $V_{F3} = 0$, and the dotted line shows $G(V_{SG})$ when $V_{F1} = 0$ V, $V_{F2} = 0$ and $V_{F3} = -0.3$ V. The dashed line shows $G(V_{SG})$ when $V_{F1} = -0.22$ V, $V_{F2} = 0$ V and $V_{F3} = -0.3$ V, so that we have 0.7 structure present in two 1D channels in series. The measurement temperature was 1.2 K.

From the source-drain biased measurements we know that $\Delta E_{1,2} = 2.434$ meV = $\hbar\omega_y$. The difference between the first 1D subband and the conduction band edge is simply $\frac{1}{2}\hbar\omega_y$ in a simple harmonic oscillator. Thus we calculate ω_y to be 3.698×10^{12} s⁻¹ and $U(0)$ to be 5.78 meV. The 1D channel width can be estimated when the energy of the first 1D subband crosses the Fermi energy in the bulk 2DEG ($E_F = 7$ meV). From this we calculate that the constriction width underneath F1 (F3) at the Fermi energy to be 43.3 nm. As shown in Fig. 4, we can see that the 0.7 structure is still observed when the two 1D constrictions are in series but at occurs at a slightly less negative V_{SG} . This is to be expected since two gate fingers are being biased rather than one and there is a small degree of cross talk between F1 and F3. The ratio of the reduction of pinch-off voltage to the initial pinch-off voltage is only $0.04/2.65=1.5\%$. If the 0.7 structure were a transmission effect, then when we have 0.7 structure present in two 1D channels in series, a shoulder like structure close to $0.7 \times 0.7 = 0.49(2e^2/h)$ should be observed. Instead, the 0.7 structure persists

and behaves as if it is like two ballistic resistors in series as first studied by Wharam *et al.* [18] and reproduced here. Thus our experimental results show that the 0.7 structure is *not* a transmission effect through a clean one-dimensional channel at zero in-plane magnetic field.

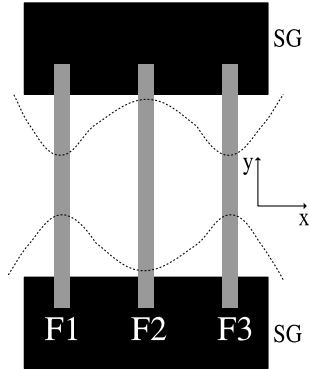


FIG. 5. A schematic diagram showing that applying negative voltages on F1 and F3 creates two narrower 1D constrictions in series. The dotted lines indicate the depletion regions.

In conclusion, we have shown further supporting evidence that 0.7 structure is an intrinsic property of a clean one-dimensional channel, even when quantized ballistic plateaus are no longer distinguishable for weak lateral confinement. Moreover, we have shown that the 0.7 structure is *not* a transmission effect at zero in-plane magnetic field.

This work was funded by the UK EPSRC, and in part, by the US Army Research Office. We thank C.H.W. Barnes, J.T. Nicholls, K.J. Thomas and in par-

ticular C.J.B. Ford and J.H. Davies for fruitful discussions, and J.D.F. Franklin, J.E.F. Frost and H.D. Clark for advice and help on device fabrication at an early stage of this work. G.H.K. acknowledges financial support from the Skillman Fund, Clare College. D.A.R. acknowledges support from Toshiba Research Europe Ltd.

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